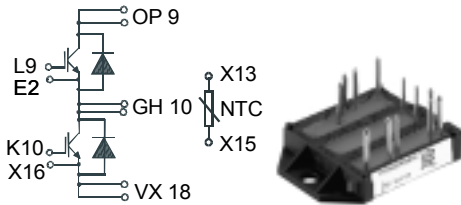


IGBT Module

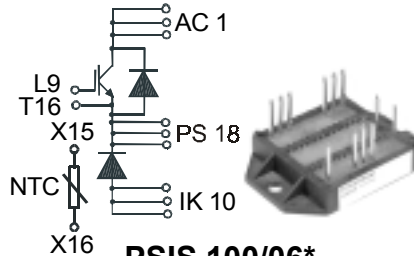
Preliminary Data Sheet

PSIG 100/06
PSI 100/06*
PSIS 100/06*
PSSI 100/06*

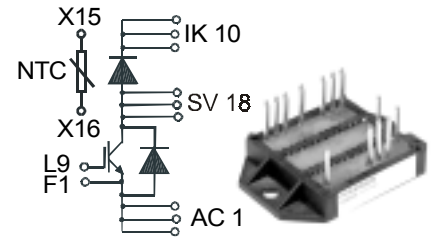
I_{C25} = 93 A
 V_{CES} = 600 V
 $V_{CE(sat)typ.}$ = 2.4 V



PSI 100/06*



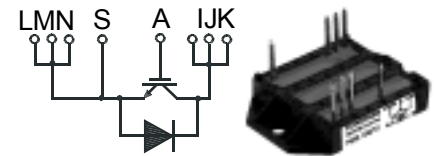
PSIS 100/06*



PSSI 100/06*

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	93	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	63	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100\ \mu\text{H}$	150	A
		V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	294	W



PSIG 100/06

*NTC optional

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.4	2.8	V
$V_{GE(th)}$	$I_C = 1.5\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.4	6.5 mA
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$		150	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}; I_C = 60\text{ A}$ $V_{GE} = 15/0\text{ V}; R_G = 15\ \Omega$	150		ns
		60		ns
		450		ns
		40		ns
E_{on} E_{off}		3.2		mJ
		2.2		mJ
C_{ies}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$	4.2		nF
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 μm)	0.85		0.43 K/W K/W

Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	134	A
I_{F80}	$T_C = 80^\circ\text{C}$	82	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 60\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.78	1.99	V
I_{RM} t_{rr}	$I_F = 60\text{ A}; di_F/dt = 500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	28		A
		100		ns
R_{thJC} R_{thJH}	with heatsink compound (0.42 K/m.K; 50 μm)	1.32		0.66 K/W K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25} $B_{25/50}$	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k Ω K

Module

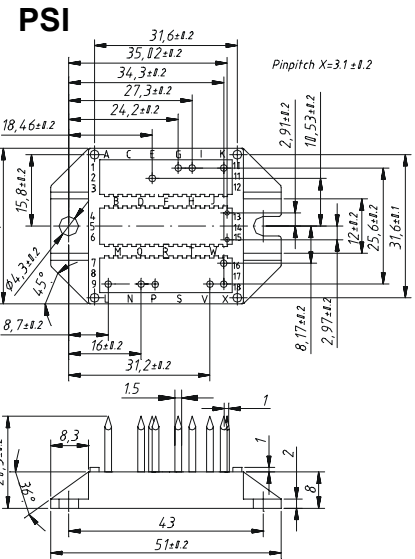
Symbol	Conditions	Maximum Ratings	
T_{VJ} T_{stg}		-40...+150	$^\circ\text{C}$
		-40...+150	$^\circ\text{C}$

V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	3000	V~
M_d	Mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.
a	Max. allowable acceleration	50	m/s^2

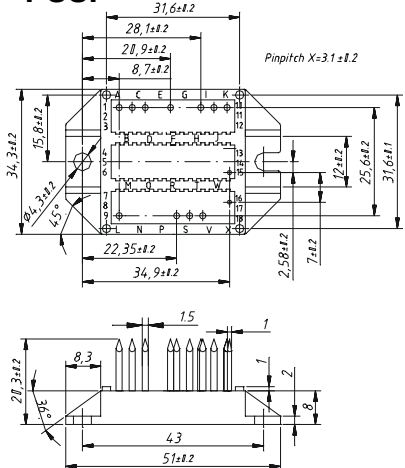
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		24		g

Package style and outline

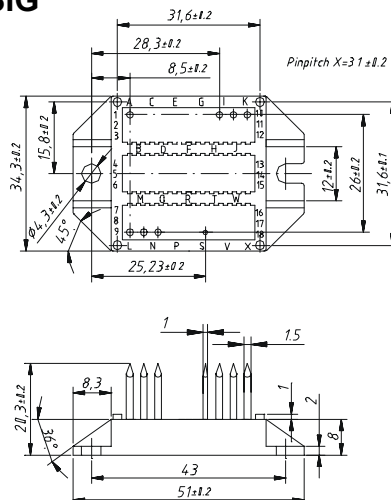
Dimensions in mm (1mm = 0.0394")



PSSI



PSIG



PSIS

